

# SANYO Semiconductors DATA SHEET

P-Channel Silicon MOSFET

# **CPH3338**— General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 4V drive.

# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ΙD		-3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-14	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-30			٧
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A	2.4	4		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =-2A, V <sub>G</sub> S=-10V		57	74	mΩ
	RDS(on)2	ID=-1A, VGS=-4.5V		101	141	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-1A, V <sub>G</sub> S=-4V		118	165	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, f=1MHz		566		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		101		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-10V, f=1MHz		84		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		11		ns
Rise Time	tr	See specified Test Circuit.		13		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		49		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		36		ns

Marking: YN Continued on next page.

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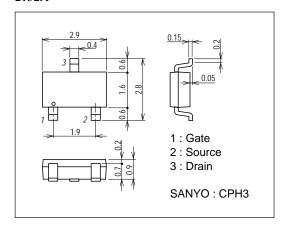
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	O IIII
Total Gate Charge	Qg	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.5A		11.7		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.5A		2.04		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.5A		2.64		nC
Diode Forward Voltage	VSD	IS=-3.5A, VGS=0		-0.86	-1.2	V

### **Package Dimensions**

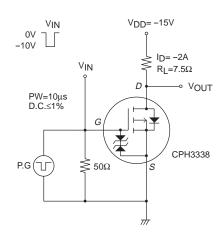
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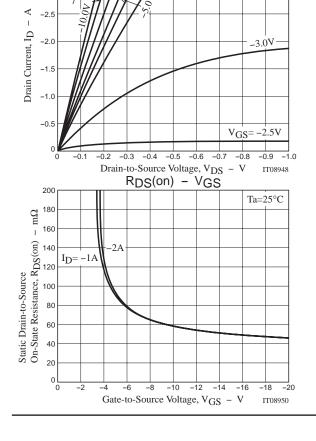
-3.5

-3.0

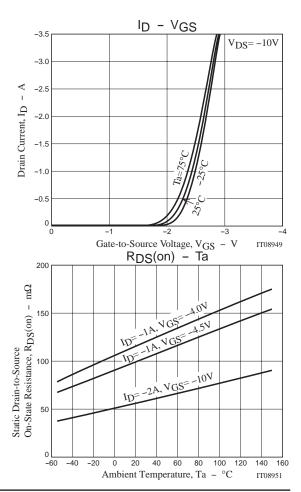


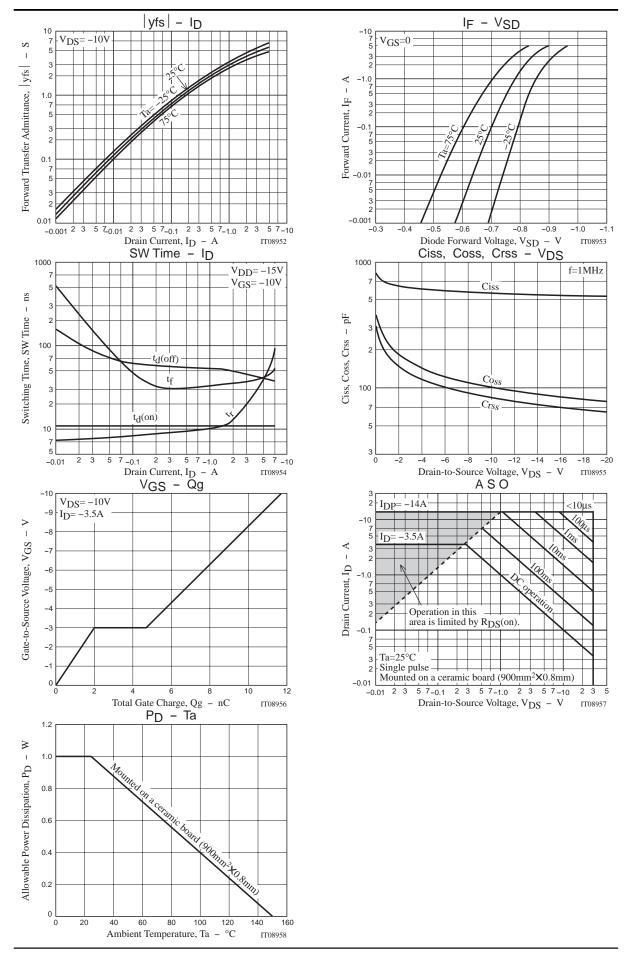
## **Switching Time Test Circuit**





ID - VDS





Note on usage: Since the CPH3338 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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